

Supporting Information

Electrical Characteristics of Metal Catalyst- Assisted Etched Rough Silicon Nanowire Depending on the Diameter Size

*Sang Hoon Lee^{‡, a}, Tae Il Lee^{‡, b}, Su Jeong Lee,^a Sang Myung Lee,^c Ilgu Yun,^c and Jae Min
Myoung^{*a}*

^aDepartment of Materials Science and Engineering, Yonsei University, Seoul, Korea

^bDepartment of BioNano Technology, Gachon University, Seongnam, Korea.

^cDepartment of Electrical and Electronic Engineering, Yonsei University, Seoul, Korea

Corresponding Author

*E-mail: jmmyoung@yonsei.ac.kr

Supporting Figures

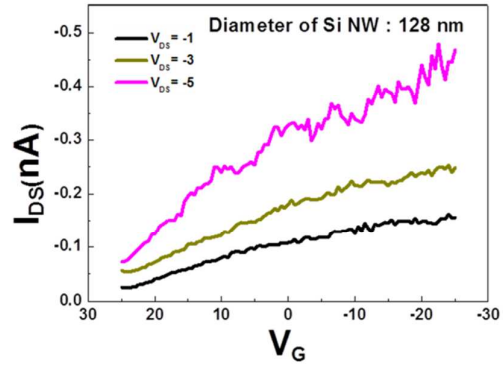


Figure S1. The electrical property (transfer curve) of Si NW FET without hydrazine treatment.

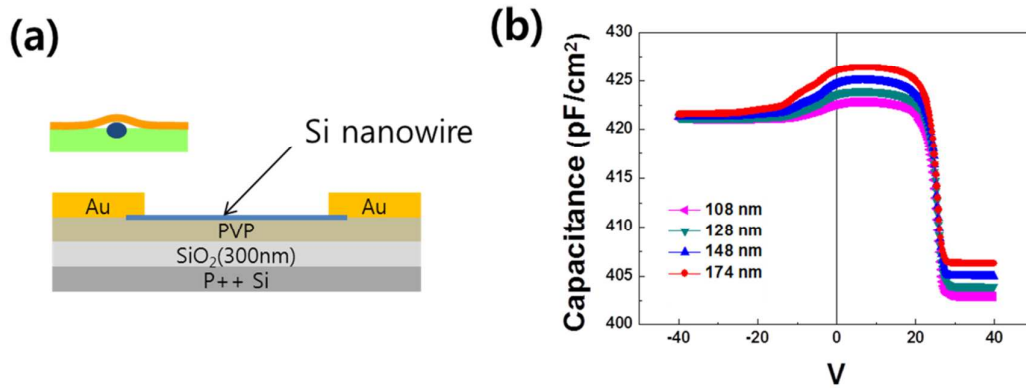


Figure S2. (a) The structure of device for simulating capacitance of a Si NW-embedded gate insulator and (b) its result along to various diameters of embedded Si NW.

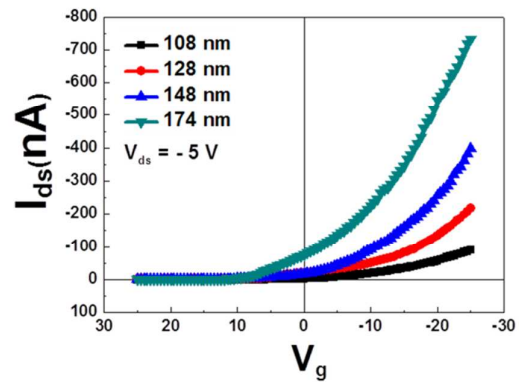


Figure S3. The transfer characteristic of Si NW FET with varying the diameter of Si NW embedded in PVP layer.